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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)

Attorney Docket Number: 5308-389

Serial No.: To be determined 10/772882

Applicants: Adam William Saxler

Filing Date: Concurrently herewith

Group: Uknown

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	Application Number	10/772,882	
	Filing Date	February 5, 2004	
	First Named Inventor	Saxler	
•	Group Art Unit	2811	
	Examiner Name	Jerome Jackson Jr.	
	Attorney Docket Number	5308-389	

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Application Number	10/772,882						
Filing Date	February 5, 2004						
First Named Inventor	Saxler						
Group Art Unit	2815						
Examiner Name	Jerome Jackson, Jr.						
Attorney Docket Number	5308-389						

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STATE	STATEMENT BY APPLICANT			First Named Inventor	Saxler	
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INFOR	MATION [DISCLOSUR	RE	Filing Date	February 5, 2004	
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		OTHER NON PATENT LITERATURE DOCUMENTS					
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		13.		Group Art Unit	2811
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Filing Date	February 5, 2004					
First Named Inventor	Adam Saxler					
Group Art Unit	2815					
Examiner Name	Jerome Jackson, Jr.					
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